

Preface

These volumes contain written versions of papers which were presented at the International Conference on Silicon Carbide and Related Materials 1999 (ICSCRM'99), held October 10-15, 1999 in Research Triangle Park, North Carolina. Over 650 participants from 25 countries attended the conference. This attendance was the highest in the conference series to date.

This record attendance and the large number of papers submitted attest to the rapidly increasing interest in wide bandgap semiconductors in both academic and industrial communities. Contained in the two volumes of these proceedings are 401 papers, 19 of which were invited. They document our present understanding of the many topics of interest, such as the growth of bulk crystals, the growth of epitaxial layers, theoretical approaches, materials characterization, device processing and design, fabrication and characterization of electronic and optoelectronic devices, some with outstanding performance.

The success of the conference was due in large part to the labor of many people on the various committees as well as the generous support of four U.S. Government and thirteen industrial sponsors. We wish to thank the students from the University of Pittsburgh (Song Bai, Oleg Shigiltchhoff, and Yevgeniy Shishkin) and Carnegie Mellon University (S.-Y. Ha, T. Jang, T. Kuhr, and E. Sanchez) for their hard work in getting the papers organized and reviewed. We also wish to thank the students from the University of South Carolina for helping the session chairpersons and handling the microphones for questions during the conference. Finally, we thank the staff of the North Carolina State University Department of Continuing Education for their hard work in organizing the conference, especially Connie McElroy-Bacon, Cindy Allen and Dee Dee Coon.

The next conference will be held in October, 2001 in Tsukuba, Japan. Prof. S. Yoshida of Saitama University will chair the Organizing Committee, Prof. H. Matsunami of Kyoto University will chair the International Steering Committee and Prof. S. Nakashima of Miyazaki University will chair the Sponsor Committee. We wish the organizers of the next conference much success.

Calvin H. Carter, Jr.

Robert P. Devaty

Gregory S. Rohrer

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